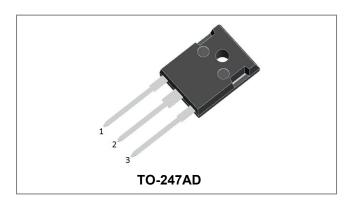


Technical Data Data Sheet N1729, Rev. A





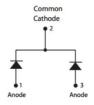
MBR8060WT SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	60	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=120°C, rectangular wave form	40(Per Leg) 80(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	600	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V_{F1}	@ 40A, Pulse, T _J = 25℃	-	0.65	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R ,T _J = 25℃	-	40	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25^{\circ}C,$ $f_{SIG} = 1MHz$	-	2500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%



Technical Data Data Sheet N1729, Rev. A

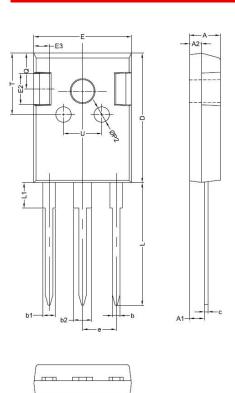


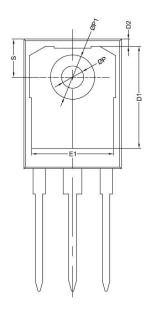


Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _θ JC	DC operation	0.8	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Mechanical Dimensions TO-247AD





OVMBOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2		1.20			
Е	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
Q S T	6.05	6.15	6.25		
T		10.00			
U		6.20			

Ordering Information:

Device	Package	Shipping	
MBR8060WT	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •



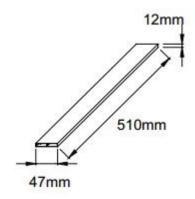


Technical Data Data Sheet N1729, Rev. A





Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type 80 = Forward Current (80A) 60 = Reverse Voltage (60V) WT = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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